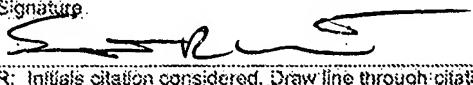


Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No: 10559-586002	Application No. 10/802,331
Information Disclosure Statement by Applicant (Use separate sheets if necessary) (37 CFR §1.98(b))		Applicant: Lawrence D. Wong	
		Filing Date March 16, 2004	Group Art Unit 2826

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
Su	AA	4,848,141	07-1989	Oliver et al.	73	81	
Su	AB	6,340,628	01-2002	Van Cleemput et al.	438	586	
	AC						
	AD						

Foreign Patent Documents or Published Foreign Patent Applications							
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation Yes <input type="checkbox"/> No <input checked="" type="checkbox"/>
	AE						
	AF						
	AG						

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
Su	AH	Hara et al., "Mechanism of Mechanical and Chemical Polishing in Low Dielectric Constant Plasma-Enhanced Chemical Vapor Deposition SiOC Layer from hexamethyldisiloxane", Electrochem. And Solid State Lett., 4(8):65-67 (Aug. 2001).
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Examiner Signature 	Date Considered 7/5/2007
EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	